

CLAIMS

What is claimed is:

- 5 1. A high-Q on-chip inductor comprises:
- primary winding including a first node and a second node,
wherein the primary winding has a first admittance; and
- 10 auxiliary winding including a first node and a second node,
wherein the auxiliary winding has a second admittance,
wherein the second node of the primary winding is coupled
to the second node of the auxiliary winding, wherein the
second admittance is greater than the first admittance,
- 15 wherein the first node of the primary winding is operably
coupled to receive a first leg of an input, wherein the
second node of the primary winding is coupled to receive a
second leg of the input, and wherein the first node of the
auxiliary winding is coupled to receive a proportionally
- 20 opposite representation of the first leg of the input.
2. The high-Q on-chip inductor of claim 1, wherein the
first admittance includes first self admittance and first
coupled admittance and wherein the second admittance
- 25 includes second self admittance and second coupled
admittance.
3. The high-Q on-chip inductor of claim 2, wherein the
auxiliary winding is proximally located to the primary
- 30 winding to at least partially establish the first and
second coupled admittances.

4. The high-Q on-chip inductor of claim 2, wherein the auxiliary winding is asymmetric with respect to the primary winding to at least partially establish the second admittance being greater than the first admittance.

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5. The high-Q on-chip inductor of claim 4, wherein the asymmetry is achieved by at least one of: asymmetrical electromagnetic coupling between the primary winding and the auxiliary winding, asymmetrical number of turns between
10 the primary winding and the auxiliary winding, and asymmetrical geometric configuration of the primary and auxiliary windings.

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6. The high-Q on-chip inductor of claim 1 further comprises a poly-silicon shield operably coupled to the primary winding and to the auxiliary winding.

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7. The high-Q on-chip inductor of claim 1 further comprises:

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the primary winding including a plurality of turns on multiple dielectric layers of an integrated circuit, wherein the plurality of turns are operably coupled via bridges on differing dielectric layers of the integrated
circuit; and

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the auxiliary winding including at least one turn on at least one of the multiple dielectric layers of the integrated circuit.

8. The high-Q on-chip inductor of claim 1 further comprises:

the primary winding including at least one turn on a first dielectric layer of an integrated circuit; and

- 5 the auxiliary winding including at least one turn on a second dielectric layer of the integrated circuit, wherein the at least one turn of the primary winding is stacked with respect to the at least one turn of the auxiliary winding.

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9. A high-Q on-chip inductor comprises:

primary winding including a first node and a second node;
and

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auxiliary winding operably coupled to increase a quality
factor of the primary winding.

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10. The high-Q on-chip inductor of claim 9, wherein the
auxiliary winding is proximally located to, and reversed
biased with respect to, the primary winding to at least
partially establish an admittance of the auxiliary winding
to be greater than an admittance of the primary winding.

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11. The high-Q on-chip inductor of claim 9, wherein the
auxiliary winding is asymmetric with respect to the primary
winding to at least partially establish an admittance of
the auxiliary winding being greater than an admittance of
the primary winding.

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12. The high-Q on-chip inductor of claim 11, wherein the
asymmetry is achieved by at least one of: asymmetrical
electromagnetic coupling between the primary winding and
the auxiliary winding, asymmetrical number of turns between
the primary winding and the auxiliary winding, and
asymmetrical geometric configuration of the primary and
auxiliary windings.

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13. The high-Q on-chip inductor of claim 9 further
comprises a poly-silicon shield operably coupled to the
primary winding and to the auxiliary winding.

14. The high-Q on-chip inductor of claim 9 further comprises:

5 the primary winding including a plurality of turns on multiple dielectric layers of an integrated circuit, wherein the plurality of turns are operably coupled via bridges on differing dielectric layers of the integrated circuit; and

10 the auxiliary winding including at least one turn on at least one of the multiple dielectric layers of the integrated circuit.

15 15. The high-Q on-chip inductor of claim 9 further comprises:

the primary winding including at least one turn on a first dielectric layer of an integrated circuit; and

20 the auxiliary winding including at least one turn on a second dielectric layer of the integrated circuit, wherein the at least one turn of the primary winding is stacked with respect to the at least one turn of the auxiliary winding.

16. A method for manufacturing a high-Q on-chip inductor comprises:

creating a primary winding to include a first node and a
5 second node, wherein the primary winding has a first
admittance; and

creating an auxiliary winding to include a first node and a
second node, wherein the auxiliary winding has a second
10 admittance, wherein the second node of the primary winding
is coupled to the second node of the auxiliary winding,
wherein the second admittance is greater than the first
admittance, wherein the first node of the primary winding
is operably coupled to receive a first leg of an input,
15 wherein the second node of the primary winding is coupled
to receive a second leg of the input, and wherein the first
node of the auxiliary winding is coupled to receive a
proportionally opposite representation of the first leg of
the input.

20 17. The method of claim 16 further comprises:

creating the primary winding to have the first admittance
that includes first self admittance and first coupled
25 admittance; and

creating the auxiliary winding to have the second
admittance that includes second self admittance and second
coupled admittance.

30 18. The method of claim 17 further comprises:

creating the auxiliary winding to be proximally located to the primary winding such that at least part of the first and second coupled admittances are established.

5 19. The method of claim 17 further comprises:

creating the auxiliary winding to be asymmetric with respect to the primary winding such that the second admittance is greater than the first admittance.

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20. The method of claim 19 further comprises creating the asymmetry by at least one of:

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asymmetrical electromagnetic coupling the primary winding to the auxiliary winding;

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creating number of turns of the primary winding to be different than a number of turns of the auxiliary winding; and

creating the primary winding to have different geometric configuration than the auxiliary winding.

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21. The method of claim 16 further comprises:

creating a poly-silicon shield that is operably coupled to the primary winding and to the auxiliary winding.

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22. The method of claim 16 further comprises:

creating the primary winding to include a plurality of turns on multiple dielectric layers of an integrated circuit,

- 5 coupling the plurality of turns via bridges on differing dielectric layers of the integrated circuit; and

creating the auxiliary winding including at least one turn on at least one of the multiple dielectric layers of the
10 integrated circuit.

23. The method of claim 16 further comprises:

- creating the primary winding to include at least one turn
15 on a first dielectric layer of an integrated circuit; and

creating the auxiliary winding to include at least one turn on a second dielectric layer of the integrated circuit in a stacked configuration with respect to the at least one turn
20 of the primary winding.

24. A method for manufacturing a high-Q on-chip inductor comprises:

creating a primary winding to include a first node and a
5 second node; and

creating an auxiliary winding operably coupled to increase
a quality factor of the primary winding.

10 25. The method of claim 24 further comprises:

creating the auxiliary winding to be proximally located to,
and reversed biased with respect to, the primary winding
such that an admittance of the auxiliary winding is greater
15 than an admittance of the primary winding.

26. The method of claim 24 further comprises:

creating the auxiliary winding to be asymmetric with
20 respect to the primary winding to at least partially
establish an admittance of the auxiliary winding being
greater than an admittance of the primary winding.

27. The method of claim 26 further comprises creating the
25 asymmetry by at least one of:

asymmetrical electromagnetic coupling the primary winding
to the auxiliary winding;

30 creating the primary winding to have a differing number of
turns than a number of turns of the auxiliary winding; and

creating the primary winding to have an asymmetrical geometric configuration with respect to the auxiliary winding.

5 28. The method of claim 24 further comprises:

creating a poly-silicon shield operably coupled to the primary winding and to the auxiliary winding.

10 29. The method of claim 24 further comprises:

creating the primary winding to include a plurality of turns on multiple dielectric layers of an integrated circuit;

15 connecting the plurality of turns of the primary winding using bridges on differing dielectric layers of the integrated circuit; and

20 creating the auxiliary winding to include at least one turn on at least one of the multiple dielectric layers of the integrated circuit.

30. The method of claim 24 further comprises:

25 creating the primary winding to include at least one turn on a first dielectric layer of an integrated circuit; and

30 creating the auxiliary winding to include at least one turn on a second dielectric layer of the integrated circuit in a stacked configuration with respect to the at least one turn of the primary winding.